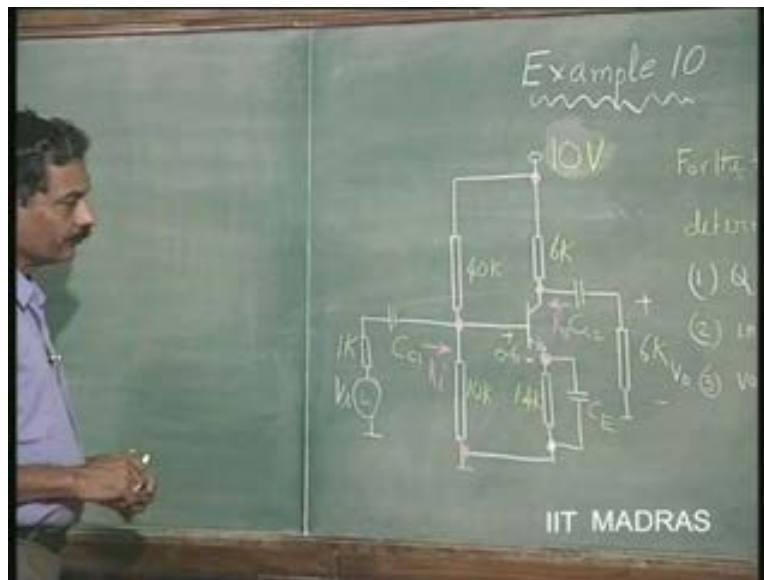


Electronics for Analog Signal Processing - I
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Lecture – 25
Transistor Biasing using Single Supply

In the last class, we had seen how dual supply arrangement can bias a transistor in the active region and how it can be used as a common emitter amplifier. Today, we will discuss an example in which the transistor is biased using a single supply. We already know how this can be made to work in the active region using a single supply. So, on working out this example, we will further clarify how it can be used as a common emitter amplifier.

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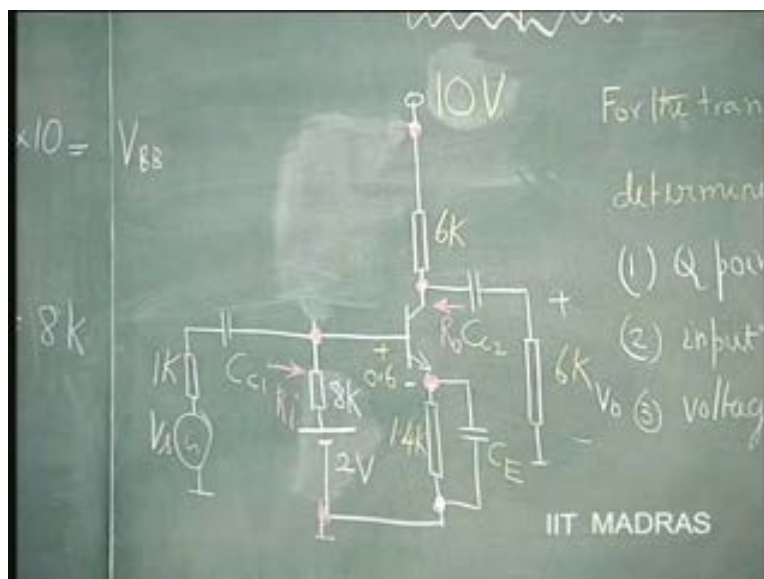
Now, using a single supply, we had seen that we have to derive another supply from this single supply, 10 volts. Another supply is derived using these two resistors, 10 K and 40 K, in this case, as 10 K divided by 10 plus 40 K of 10 volts. That is the Thevenin's voltage, which we call as V_{BB} , which we have been calling. In this case, this comes out as 2 volts; and the Thevenin's resistance which we have been calling as R_B , it comes in series with these 2 volts, is 10 K parallel 40 K, which is 8 K.

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$$\frac{10}{10+40} \times 10 = V_{BB}$$
$$= 2V$$
$$R_B = \frac{10 \times 40}{50} = 8$$

So, R_B is 8 K. That means I can now replace this circuit for D.C. It will be exactly equivalent to a resistance of 8 K in series with a battery of 2 volts.

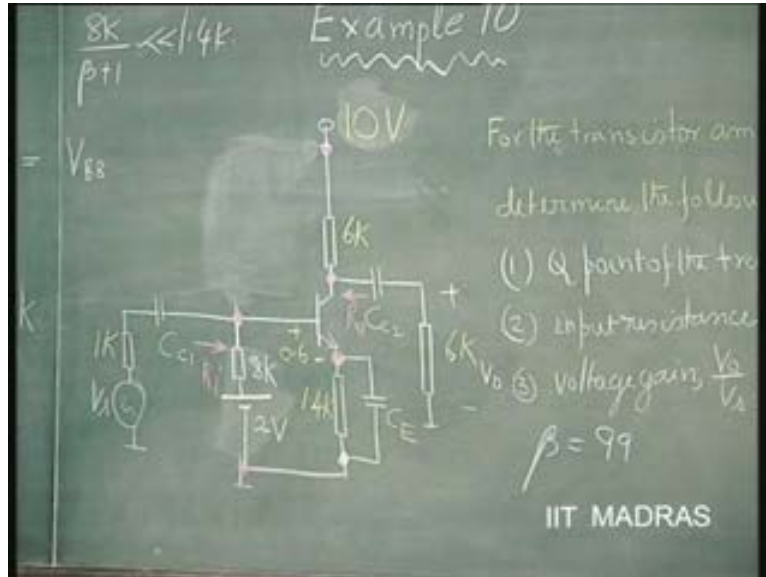
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So, that is how we are able to forward bias a transistor by means of these tools. We should, in this case, have an arrangement such that this 8 K into Beta plus, 8 K divided by Beta plus 1 should be much less than 1 point 4 K. That is, 8 K divided by Beta plus 1

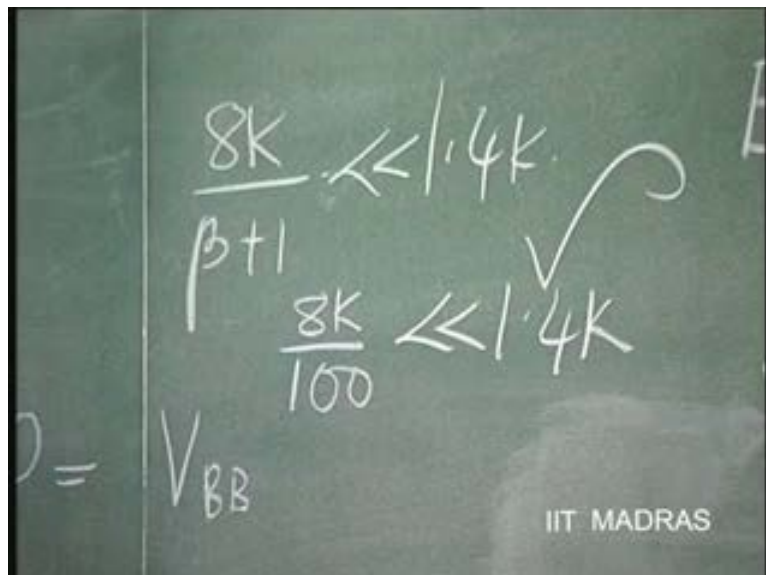
equal to, this should be much less than 1 point 4 K, in order that we can neglect the D C drop that is occurring across 8 K. This also we have seen. Let us assume, for the transistor, Beta is, let us say, 99, we will take.

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Then, in this case, we have 8 K divided by 100, is definitely much less than 1 point 4 K. So, this is valid assumption.

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Or, 8 K is much less than 140 K . So, this is valid. That means, this can be neglected; the V_{CE} drop due to base current can be neglected, and this voltage can be assumed to be at 2 volts. So, now that we know that this is going to be at 2 volts, this is point 6 volts V_{BE} . So, this voltage is 1 point 4 volts. So, 1 point 4 volts across 1 point 4 K gives a current of 1 milliamperere.

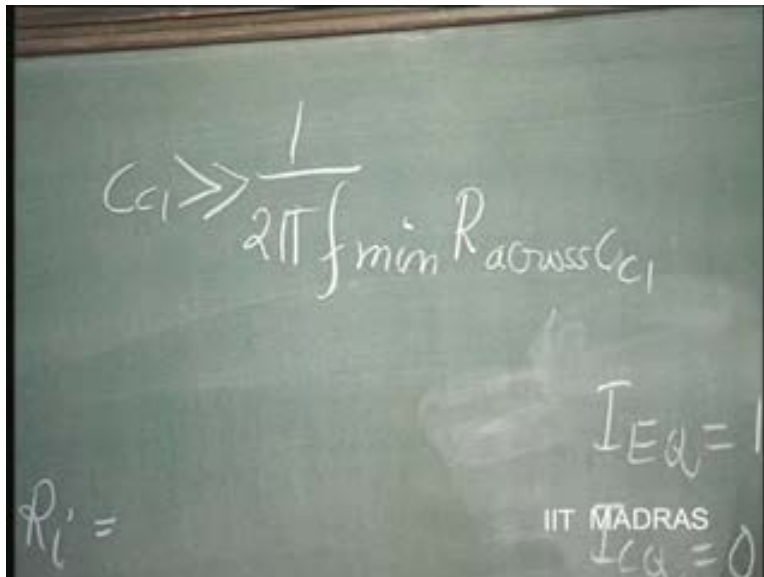
So, we know that I_{EQ} is equal to 1 milliamperere, because we have 1 point 4 volts across 1 point 4 K . So, now the operating point is therefore I_{CQ} , is equal to point 9; that is, 9 milliamperere. That is Alpha, which is Beta divided by Beta plus 1; 99 by 99 plus 1 – point 99. So, Alpha times I_{EQ} . And V_{CE} equals 10 volts minus 6 K into point 99 milliampereres. So, this voltage V_{CE} is going to be 10 minus point 99 into 6; that is, 10 – this is going to be very nearly equal to 4 volts; or, actually speaking, how much is it? 4 point 06 volts.

So, this is at 2 volts; this is at 4 volts or 4 point 06 volts. So V_{CE} , which is an important... V_{CEQ} is going to be equal to this 4 point 06 minus 2. So, we have fixed up the operating point; Q point of the transistor, I told you, measured in terms of I_{CQ} and V_{CEQ} ; forward, that it is forward biased is illustrated by the value of I_{CQ} . That it is reverse biased is illustrated by the value of V_{CEQ} .

Similarly, there is a coupling capacitor used to couple the actual load on to the collector. So, again, this is because this is at a DC of 4 point 06 volts. This is going to decouple this. How does it happen? – because, the capacitor here gets charged to 2 volts. This capacitor gets charged to 4 point 06 volts. So, that will automatically get charged to the DC voltage and therefore you get only the A C here.

So now, this is automatically charged to these 2 volts. So, the signal voltage here is going to appear here, over and above the 2 volts. So, we have 2 volts; capacitor is a short circuit. Again, compared with what? Always, $C C 1$ should be much greater than $\frac{1}{2\pi f_{min} R_{across C C 1}}$. This is what we have used for C E also; design of C E. So, under the minimum frequency of interest, the capacitors should be so chosen that it is much greater than $\frac{1}{2\pi f_{min} R_{across C C 1}}$.

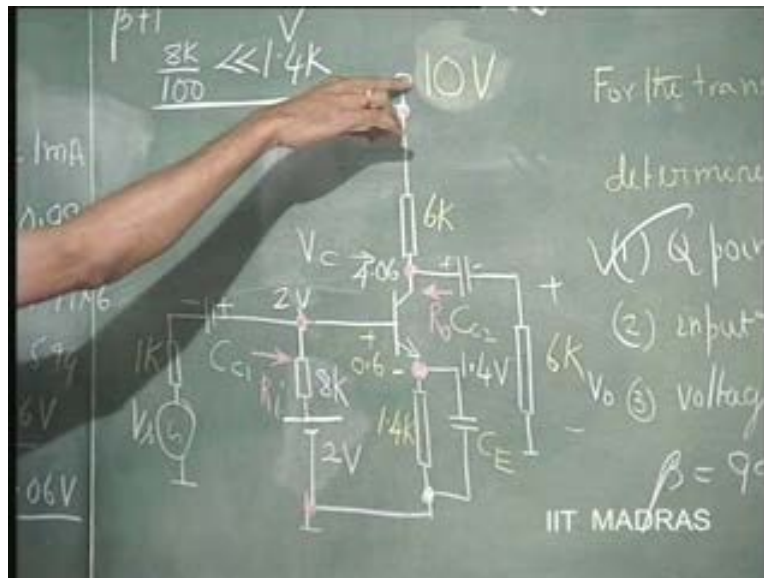
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That is done. It is a short circuit. Then, we have 8 K and this is at a constant potential; and therefore, this is a short. Then, we come to the base, **base**. Then we have r_e , the small signal resistance of the transistor between base and emitter and emitter is grounded through the capacitor; and we know how to select that value of capacitance.

So then, we have the current source, dependent current source. If this is signal current i_e , this current is going to be βi_b . So, we come to the collector point; this collector point. From here, we have 6 K to ground because this is a constant voltage; and from that, again, we have a short circuit to another 6 K .

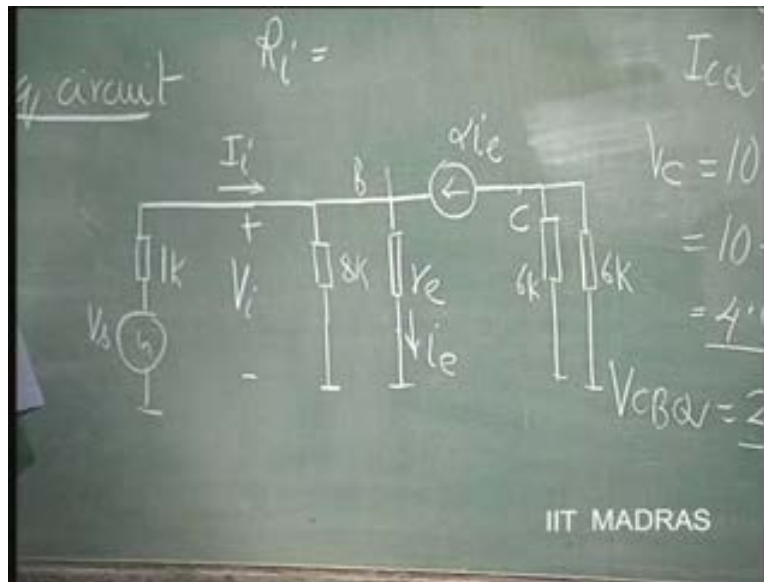
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So, we have 6 K parallel 6 K . This is supposed to be the equivalent circuit of our amplifier. Is it clear?

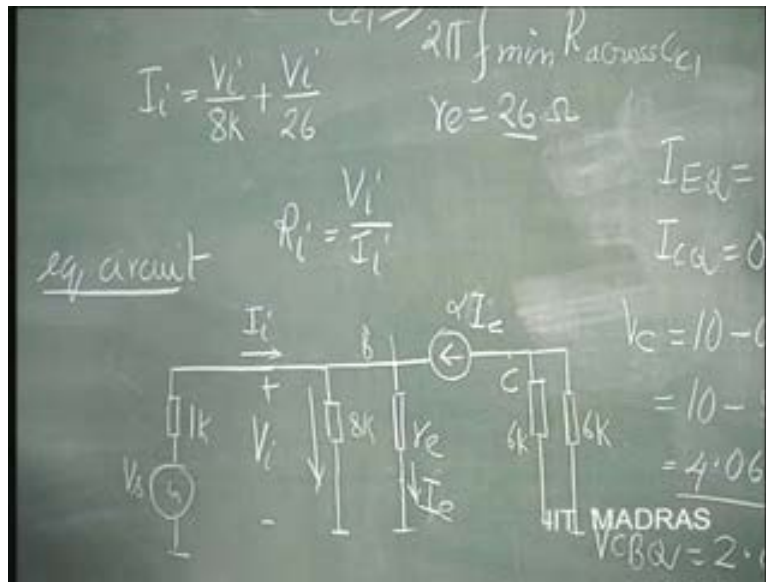
Now, if this is v_s and we have r_s , this we will call as... now, instead of using all these symbols like ΔV_i and all that, we have agreed that we will use r_{ms} value of voltages here. Since most of this analysis is done for sinusoidal signals, we will use the r_{ms} value of voltage. That is represented by V , capital V , small v ((i Refer Slide Time: 13:10)). So, input voltage here is V , capital V divided by i ; and the current here is I_i , which we have been earlier calling as Δi , v , etcetera.

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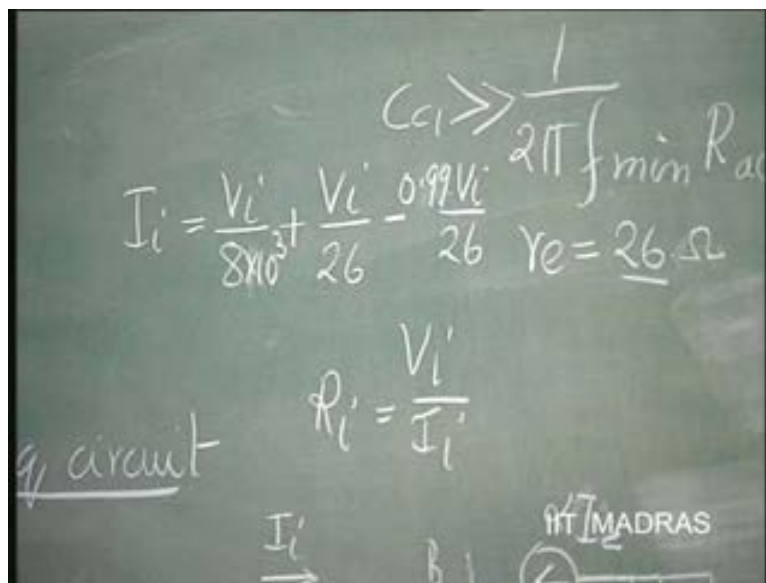
So similarly, we will convert this into what? – I_e ; and this one into r m s values, I_c . So, this current here is going to be V_i divided by $8K$; and this is V_i by r_e . So, the total current I_i ... this is nothing but V_i by I_i ; input resistance here is input voltage V_i divided by input current, that is the input resistance. So, I_i – we will write in terms V_i now. So, I_i is equal to... this current is, this current plus this current minus this current. This current is in this direction. So, this current is V_i by $8K$ plus V_i by r_e . r_e is how much? It is operating at 1 milliamperes. So, r_e is equal to 26 ohms. 26 millivolts divided by 1 milliamperes.

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So, this is going to be 26 ohms. Or, we will write down everything in terms of ohms. V_i by 26 minus Alpha times I_e . What is I_e ? V_i by r_e . I_e is equal to V_i divided by r_e . So, same thing... Alpha times V_i by 26. Alpha is already given as point 99. So, this equation straight away gives us the input resistance.

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Actually, this is going to give you... I_i by V_i therefore equals 1 over 8000 plus 1 over 26 into 1 minus α , which is point zero 1 . Actually, therefore, this is equal to 1 over 8000 ohms in parallel with 1 over 2600 ohms. This is 1 by 26 into 1 minus point 99 , which is point zero 1 .

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The chalkboard shows the following derivations:

$$\frac{I_i}{V_i} = \frac{1}{8000} + \frac{0.01}{26}$$

$$= \frac{1}{8000} + \frac{1}{2600}$$

eq. circuit

$$I_i = \frac{V_i}{8000} + \frac{V_i}{26} - \frac{0.99V_i}{26}$$

$$R_i = \frac{V_i}{I_i}$$

At the bottom, there is a partial circuit diagram with a current I_i entering a node and the text "IIT MADRAS" written below it.

So, you can see that R_i is nothing but 2.6 K parallel 8 K, so many Kilo ohms. How much is this? Please calculate this. This is about, around 2 K, 1 point 95 K.

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eq. circuit

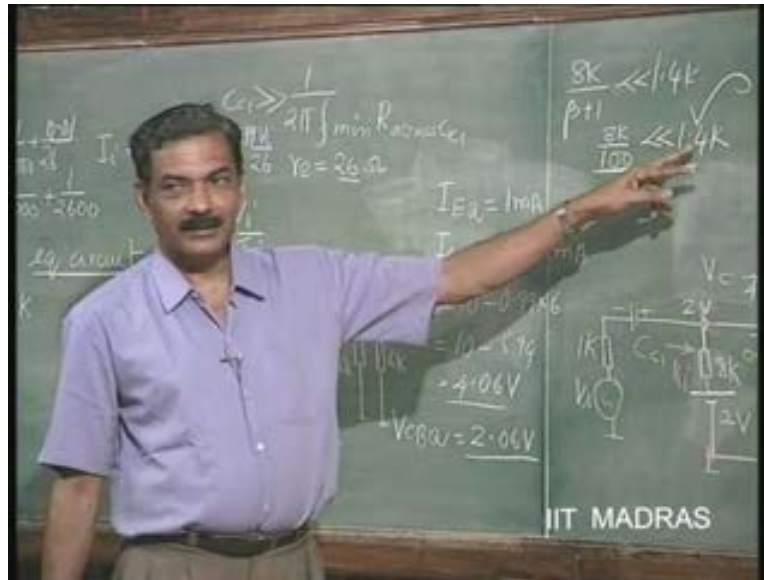
$$R_i = \frac{2.6 \times 8}{10.6} \text{ K}$$
$$\approx \underline{1.95 \text{ K}}$$

IIT MADRAS

So, that is the input resistance offered by our amplifier. Please note that it is 8 K which is coming straight away here and whatever is offered by the amplifier as 2 point 6 K. So, this 8 K is also taking away certain amount of the signal current. Actually, in order that this should not take any signal current, it should have been of the order of 10 times 2 point 6 K or so; 26 K. So, the design is not good.

If you make it too high, then it will not satisfy this relationship. If you make it 26 K, it will not satisfy this relationship.

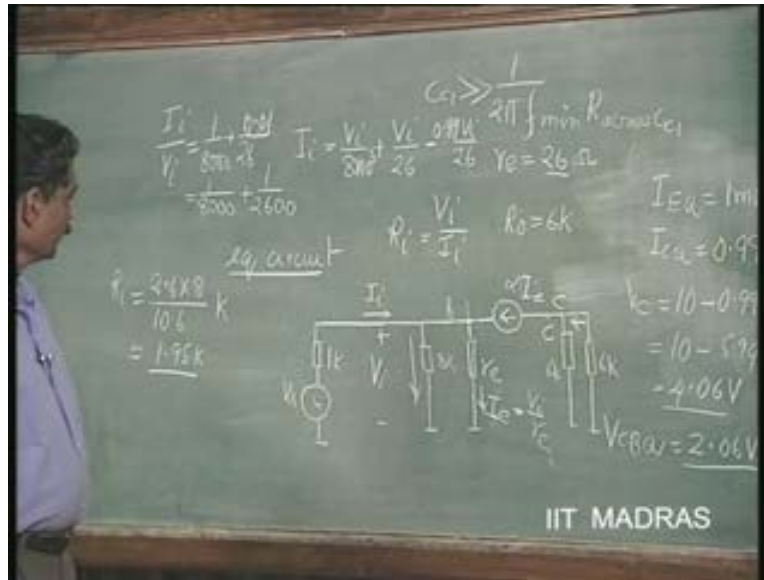
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So, this will no longer be a stable 2 volts. So, these are the compromises that are made in the design. Does not matter. Some amount of signal is going to be lost because this bias resistance is going to take away certain amount of current. So, what is now the gain? This also is over – input resistance. Output resistance is very simple.

We are looking at... if from this side that we are looking at it... from here; that is, this is the 6 K load and this is the collector point. We are looking into the collector. So, this is a current source which is excited by the input. So, that current source is not at all there, when you are exciting it by the output. So just the 6 K resistance is going to be the output resistance. So, output resistance is equal to 6 Kilo ohms. Simple.

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Now, the voltage gain is nothing but V_{naught} , which is, this voltage divided by V_i . This is one voltage gain. What we are asked is V_{naught} by V_s . That can be very neatly put down as... V_{naught} by V_s is going to be V_{naught} by V_i into V_i by V_s . This was how we have been doing. V_{naught} by V_i into V_i by V_s .

V_i by V_s ... This is V_{naught} by V_i into... What is V_i by V_s ? If this is R_i , so, R_i by R_i plus R_s . So, R_i by R_i plus R_s , potential divider action; because this is R_i ; we have replaced it by an equivalent input resistance; R_i by R_i plus R_s is V_i by V_s . So, it is left for us to determine V_{naught} by V_i , because we know, R_i is this 1 point 95 K and R_s is 1 K. So, this is equal to V_{naught} by V_i into 1 point 95 divided by 1 point 95, plus 1 K. Now, what is V_{naught} by V_i ?

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$$\frac{V_o}{V_s} = \frac{V_o}{V_i} \times \frac{V_i}{V_s} = \frac{V_o}{V_i} \times \left(\frac{R_i}{R_i + R_s} \right)$$

$$= \frac{V_o}{V_i} \times \frac{1.95}{1.95 + 1}$$

$I_E = \alpha I_C$
 $I_C = \beta I_B$

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This also we have already determined earlier; but we will again illustrate. This 6 K parallel 6 K is 3 K. So, Alpha I_e into 3 K is minus V_{naught}. So, minus V_{naught} is equal to Alpha I_e into 3 K. Is this clear? This is assumed as plus and this as minus. So, Alpha I_e will produce plus here and minus here. So, minus V_{naught} is equal to Alpha I_e into 3 K and I_e is already known as V_i divided by r_e. So, I_e is equal to V_i divided by 26. So, this is actually 3 K, means 3000.

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$$-V_o = \alpha I_e 3000$$

$$I_e = \frac{V_i}{26}$$

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So, we get V_o over V_i equal to... from that, replacing I_e by V_i by 26, minus Alpha 3000 divided by 26; or, minus point 99 into 3000 by 26. This is roughly... please calculate this – about 120. How much is it? Point 99 into 3000 by 26 – 114, 114, minus. So, that is the voltage gain.

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The chalkboard shows the following calculations:

$$\frac{V_o}{V_i} = -\frac{\alpha 3000}{26}$$

$$= \frac{-0.99 \times 3000}{26}$$

$$= \underline{\underline{-114}}$$

$$r_i = \frac{2.6 \times 8}{10.1}$$

Additional notes on the board include:

$$\frac{I_i}{V_i} = \frac{1}{8000} + \frac{0.01}{26}$$

$$= \frac{1}{8000} + \frac{1}{2600}$$

eg, circ

IIT MADRAS

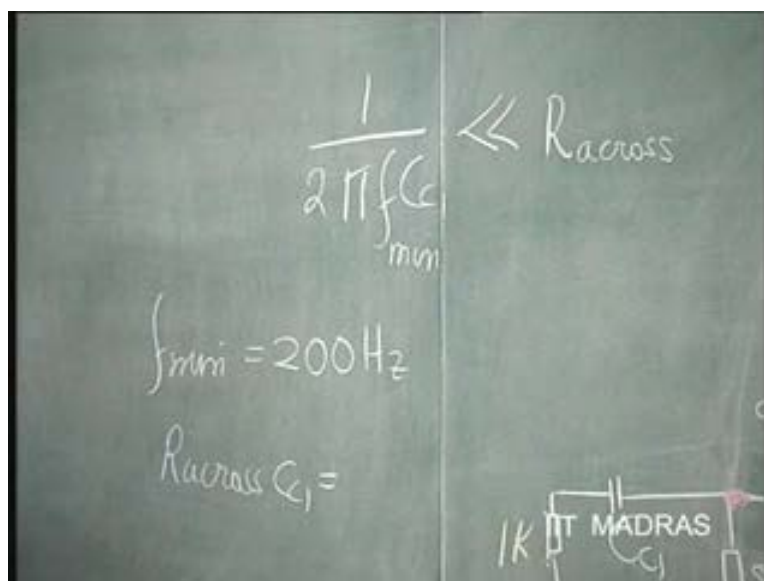
Now, I would like to further add certain questions to this example so that the complete design is understood by us. First of all, this C C 1 and C C 2 and C E... let us now exactly determine how to evaluate the value of C C 1, C C 2, C E. Now, I just said that the reactance of all these capacitors should be much less than... at the minimum frequency of interest, the resistance across. This is the basic design rule.

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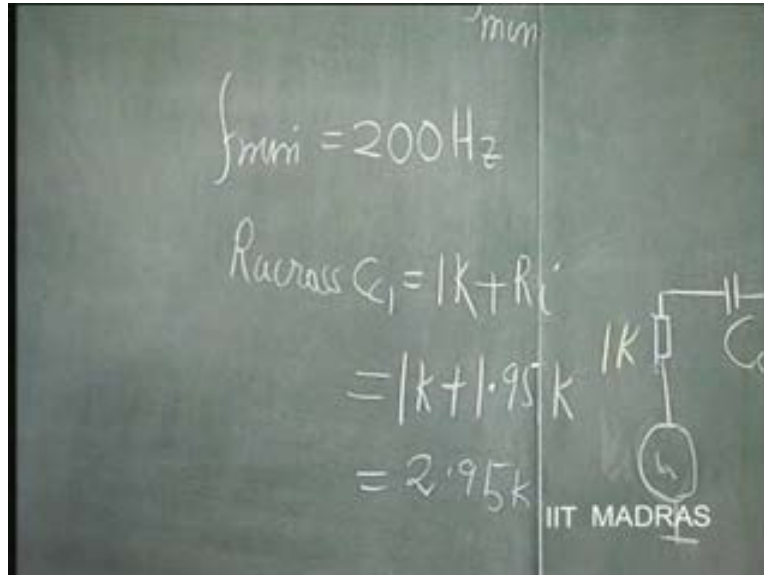
When we say much less, we will say, one tenth the short circuit means, the resistance offered by these reactances should be one tenth the resistances by these reactances. Now, let us find out in each of these cases, what this resistance is going to be. Let us assume that f_{\min} is 200 Hertz. Then, $R_{\text{across } C_1}$ equals 1 K; we can see this 1 K; then, nothing but the input resistance.

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So, 1 K plus R_i , which we have already evaluated as 1 K plus 1 point 95 K; this we had already evaluated. So, this should be 2 point 95 K; or, the resistance seen by the capacitor should be less than 295 ohms. One tenth; we will take it as one tenth.

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The resistance actually seen across the capacitor is 2 point 95 K. The resistance offered by the capacitor at the minimum frequency of interest should be of the order of one tenth; let us say, 295 ohms. That means, 295 is equal to $1 / (2\pi f_{\min} C_1)$. So, if the capacitor now offers the resistance which is 295 or less, we are happy. So, C_1 therefore is equal to $1 / (2\pi \times 200 \times 295)$. This will be 300, 6, 2000, around. Yes, how much is it? 2 point 6 microfarads.

That means, if I use any capacitor greater than 2 point 6 microfarad, it is going to satisfy this. So, this is the design rule.

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The image shows a chalkboard with handwritten mathematical derivations. On the left side, the following equations are written:
$$C_1 = \frac{1}{2\pi \times 200 \times 295}$$
$$= 2.6 \mu\text{F}$$
$$\frac{1}{2\pi \times 200 C_1} = 295$$

On the right side, the following equations are written:
$$2\pi f C_{\text{min}}$$
$$f_{\text{min}} = 200 \text{ Hz}$$
$$R_{\text{across } C_1} = 1\text{k} + R_i$$
$$= 1\text{k} + 1.95\text{k}$$
$$= 2.95\text{k}$$

At the bottom right, the text "IIT MADRAS" is visible.

Similarly, you can find out the value of C_2 as... Let us do that without going into all these equations. We know, $\frac{1}{2\pi \times 200 \times \dots}$. What is the effective resistance across this capacitor? 6 K plus output resistance. 6 K, plus output resistance which is 6 K; so, 12 K. That means, the resistance offered by the capacitor should be less than 1 point 2 K. So, this is 6 K and this is 6 K; so 12 K. One tenth of that is 1 point 2 K. So, 1 point 2 K. So, how much is this? About 10 microfarad; larger than this obviously; point, point 66 microfarad. This is about one fourth this; because, it has to offer only a resistance of 1200 ohms whereas this has to offer about 300 ohms.

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$$C_{c2} = \frac{1}{2\pi \times 200 \times 1200} = 0.66 \mu F$$

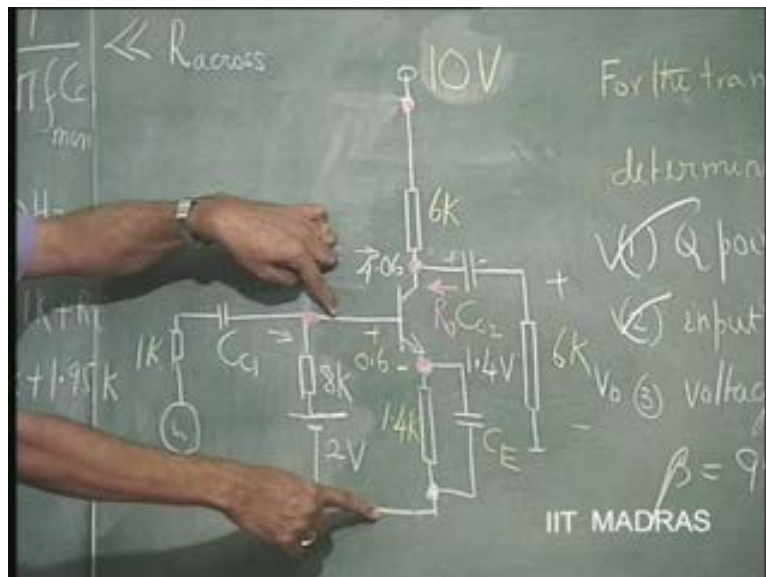
$$C_{c1} = \frac{1}{2\pi \times 200 \times 295} = 2.6 \mu F$$

$f_{min} = 200 \text{ Hz}$
 $R_{across} C_1 = 1K + R_1$

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Finally, C E. Once again, I would like to see the resistance across this capacitor. We have already done it earlier. Resistance across this capacitor is 1 point 4 K parallel r e, which is 26 ohms. Then you come here. 8 K parallel 1 K divided by Beta plus 1. Effective resistance from here to ground is 8 K parallel 1 K. That divided by Beta plus 1; because the relationship between this current and this current may vary by the factor of Beta plus 1.

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So, the resistance across C E is equal to 1 point 4 K parallel 26 ohms plus 8 K parallel 1 K divided by Beta plus 1; that is 100. So, this is going to be equal to... in fact, this resistance, 8 K parallel 1 K is 8 by 9 K; that divided by 100. So, 8 by 9 K; about 900 ohms. So, this would be offering about 9 ohms. This is offering about 9 ohms plus 26 – 35 ohms. So, we can ignore the effect of 1 point 4 K. So, this is about 35 ohms. Is this clear?

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The image shows a chalkboard with the following handwritten calculations:

$$C_1 = \frac{1}{2\pi \times 200 \times 9} = 2.6 \mu\text{F}$$

Resistance across C_E

$$= 1.4\text{K} \parallel 26 + \frac{8\text{K} \parallel 1\text{K}}{100} \parallel \frac{1}{2\pi \times 200 \times C_1} = 295$$

$$= \underline{\underline{35}}$$

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26 ohms plus 8 K parallel 1 K is 8000 by 9 K, which is 900 ohms. That divided by 100 – 9 ohms. 9 plus 26 is 35. 35 parallel 1 point 4 K is 35. So roughly, 35. You do not have to calculate these values exactly because our selection of capacitor is always going to be the higher value than whatever is given. So, 35 ohms.

That means, this capacitor should act as a short circuit and that reactance corresponds to 3 point 5 ohms. So, C E is equal to 1 over 2 pi f minimum into 3 point 5 ohms. So, somebody can calculate this. So, about 250 microfarad. How much is it? 227 microfarad.

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$$C_E = \frac{1}{2\pi \times 200 \times 3.5}$$
$$= 227 \mu\text{F}$$
$$\frac{8000}{9} = 900$$
$$C_1 = \frac{1}{2\pi \times 900}$$

Resonance across C_E

IIT MADRAS

You will see that in a typical design, it is the highest capacitor that is costlier than the other capacitor. So, this is given, which determines really the, what is called as, lower cut-off frequency. If they are not acting as short circuits, they will reduce the gain; they will take away some voltage here and some voltage here. So, they will reduce the gain and that will bring about a poor lower cut-off frequency.

If this kind of design is done, it will assure that up to 200 Hertz, the gain is not reduced at all. So, these coupling capacitors bring about a lower cut-off frequency in the amplification factor. So, the amplification will not be 114 up to very low frequencies; it will be 114 up to about 200 Hertz. Thereafter, it will come down to zero as you approach the D C. So, that brings about a lower cut-off frequency. Therefore, the lower cut-off frequency in an amplifier is always determined by these capacitors.

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Now, you can select any one of the capacitors to determine the lower cut-off frequency exactly. Other capacitors are designed to be short circuits. So, that is the way design is done. Now, the final thing about this amplifier is that, as you apply the signal, keep on applying the signal, this output will keep on getting amplified. This signal, let us say, is increasing. This is getting superimposed over 2 volts signal, but it is getting amplified by 114 or so, which is quite large.

Now, essentially therefore, you can consider that this is going to remain at 2 volts, even when the signal is present. So, this signal variation here is going to be very small compared to 2 volts. Suppose it is 1 millivolt here; here, it will be 114 millivolts. If it is 10 millivolts here, it will be 1 point 14 volts. Already this has gone up to volts range. Even then, this voltage is remaining very nearly constant at 2 volts.

So basically, we can assume for all practical purposes, this is remaining unaltered at 2 volts. But, this voltage is going to keep increasing and decreasing. When this is increasing, this will decrease; when this is decreasing, this will increase, because of the phase shift. But now, for large signal, I can still assume that this voltage remains essentially constant at 2 volts. Now, this voltage is changing from 4 point 06 volts.

Suppose I apply 10 volts. This will be swinging from 4 point 06 all the way down to 4 point 06 minus 1 point 14 and 4 point 06 plus 1 point 14, if it is assumed to be linear.

Now, I am asking you a question as to when will this go to saturation and when will it go to cut-off? So, this is some question that you have to answer. How do we answer this? We know, cut-off it reaches, when i_c becomes equal to zero; instantaneous value of current becomes equal to zero; which means, the signal swing in collector current becomes equal to I_{CQ} . This is always something that you can remember.

If this is operating at 1 milliamperes, obviously it can swing up to 2 milliamperes and zero milliamperes; around 1 milliamperes. 1 milliamperes plus 1 milliamperes – 2 milliamperes. 1 milliamperes minus 1 milliamperes – zero milliamperes. So that 1 milliamperes change may have been brought about by a disproportionate change here because of the non-linearity. Now, that is of no consequence.

So, this swing here, current swing; for it to go to cut-off is 1 milliamperes. If it is 1 milliamperes, swing peak, that is flowing into the resistance combination of 6 K into 6 K parallel 6 K which is 3 K. So, the voltage swing possible before it goes to cut-off is 1 milliamperes into 3 K, which is 3 volts. So, before it goes to cut-off, it can go to a swing of 3 volts. Is this clear?

Now, as far as the other thing is concerned, instantaneous value of V_{CB} should go to zero when it goes to saturation. The actual V_{CBQ} is 2 point 06 volts. 4 point 06 minus 2 volts. So, the voltage swing possible here is, how much is it? 2 point 06; because, when it goes from here down by an extent of 2 point 06, this potential will become same as this potential. So, 2 point 06 volts is the swing on the other side. On this side, the swing is 3 volts.

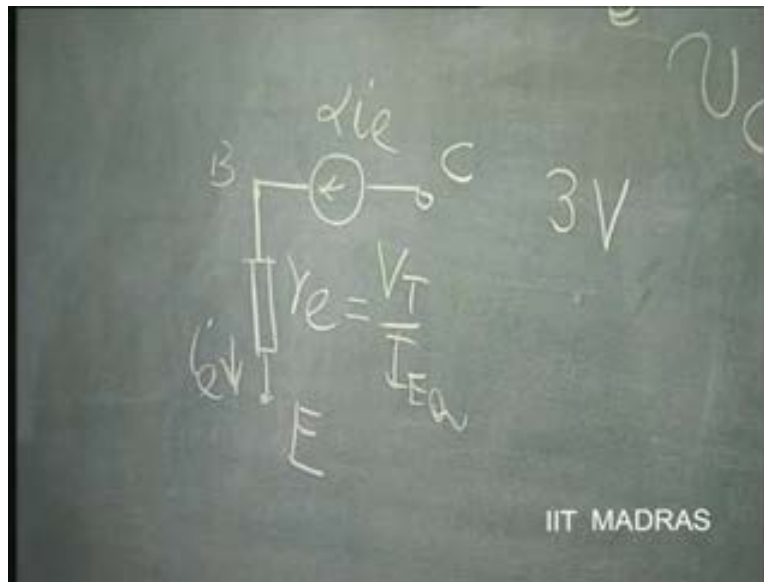
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It is asymmetric. This is not a design problem where you have been asked to design the operating point such that it is symmetric swing. What it means is the amplifier goes to what? – saturation region; the transistor goes to saturation before it goes to cut-off. If you apply a sine wave, the first distortion that will appear in this case is due to what? – saturation. So, this is important. This will not occur... It is this that is important. So, the symmetric signal swing here is how much? – 2 point 06 on either side, because here, it can go as much as 3 volts. So, it can easily go to 2 point 06. So, the lower of these two will set the limit for symmetric swing at the output.

So, with this, the complete discussion of common emitter amplifier is over. However, I would like to just say one thing. The characteristics of the transistor; we have assumed as a current source, αi_e . So, the equivalent circuit of the transistor is very simple. r_e which is equal to V_T / I_E and a current source... please, always put down this, dependent current source i_e , if it is. This is αi_e . This is the simplest equivalent circuit we have used so far.

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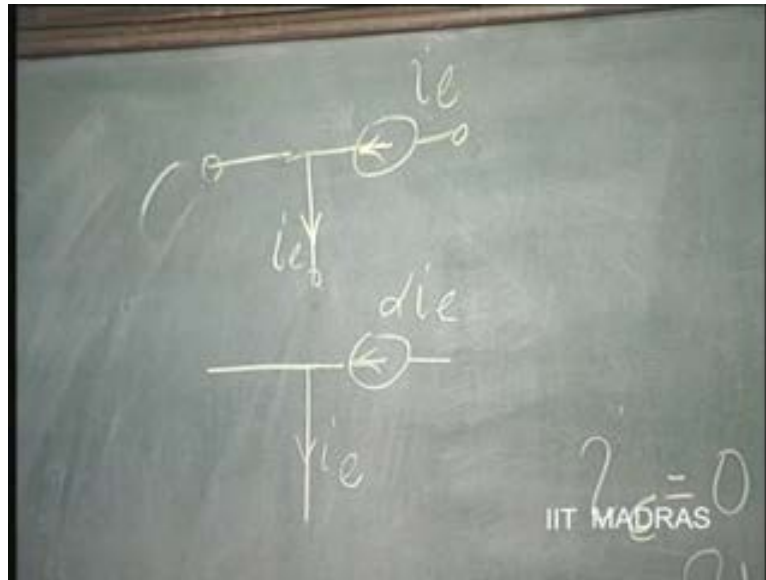


Another one simpler also we have used wherein, we just said this is a short circuit; and if this is i_e , that is αi_e . Simpler than that, which is nullator norator one; we just said this is I_e and α is equal to 1 and there is no base current at all.

So, that is the simplest equivalent circuit. So, what we said was this is a short circuit and this is αi_e ; this is i_e . This is simpler than this; and further, we just said this is i_e . This is i_e . α equal to 1. The ideal transistor equivalent circuit; and you see here, if you represent this by an equivalent circuit like this, i_e if it is taken, i_e is the current, source current here; that means, the current in this is always zero.

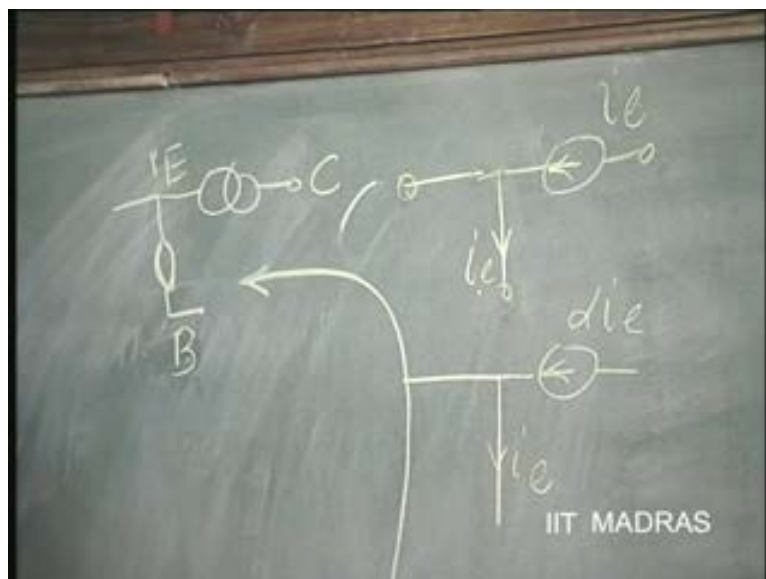
Between these two points, potential is zero, the current here is zero; and therefore, these two points were replaced by what is called a nullor; because current through this is zero, voltage across it is zero. That has been brought about by definition of an ideal transistor here. This is i_e and this is i_e ; in which case, only when this is i_e , this current is going to be zero.

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Therefore, between these two points, you represent it by a nullor and here this is a norator. This is a source which can give you any current across it; any voltage can be sustained. So, this is the root to the ideal network representation of a transistor. So, this is the base, this is the emitter; so, junction between this and the collector, this is the emitter and this is the base. Through the base, there is no current.

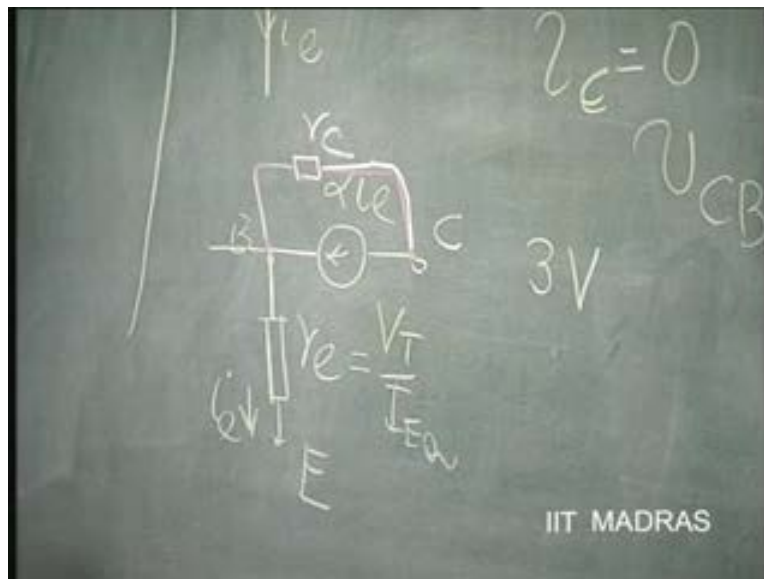
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So, you can therefore see the development of the equivalent circuit. In most of the non-ideal things, we will use this equivalent circuit. In a very big circuit, we can even use this nullator-norator equivalent. Is this understood now? This, we had already discussed earlier.

Now, I just want to modify this slightly and bring about non-ideality here. This is not a current source which is ideal; there might be a large resistance of the order of tens of megaohms across it because, it is a reverse bias junction. Collector base junction is a reverse bias junction. So, it is not a current source; there is a resistance which we will call as r_c across this. So, please remember that this is a new thing that we have brought about here. Across collector base junction, there is a resistance which is of the order of tens of megaohms, which we have been earlier ignoring.

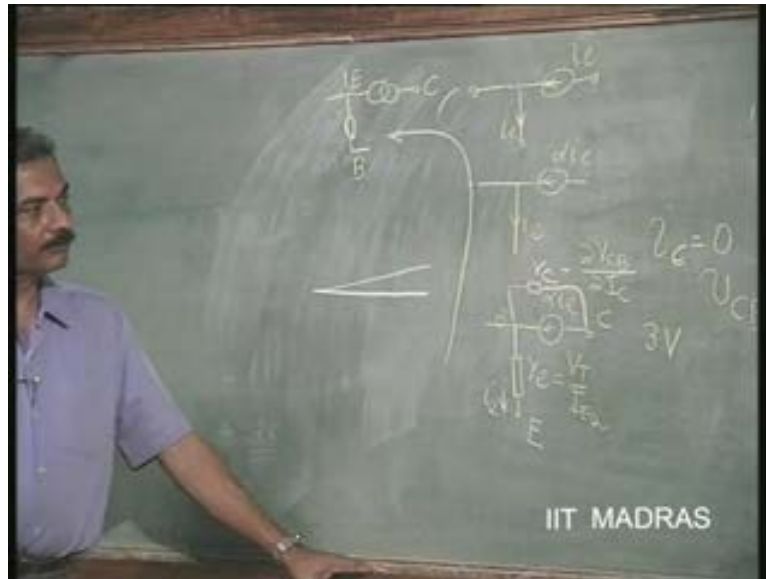
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What does this mean? That at any given operating point, we had assumed that the characteristic is an independent... it is independent of collector base voltage. But, there is a dependence on collector base voltage for this current. That is why... collector base voltage dependence comes about because of r_c . Earlier, it was independent of collector base reverse bias voltage; but there is a dependence on collector base voltage now; and

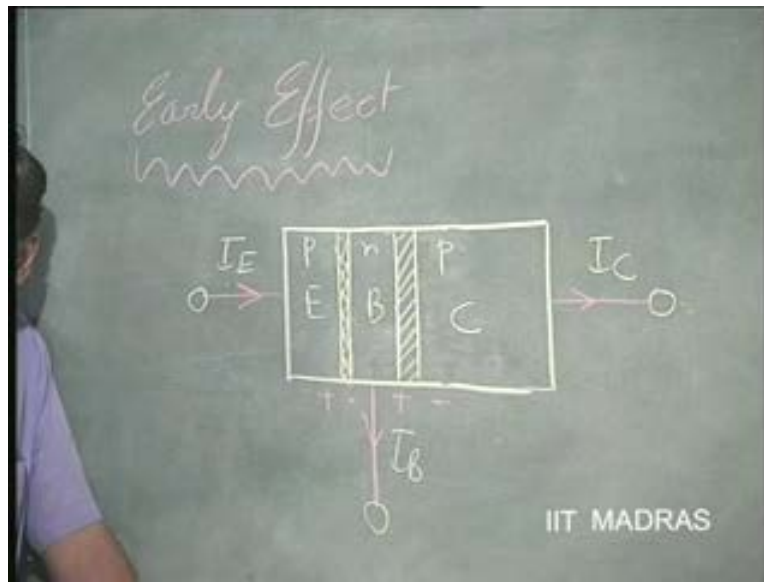
this slope at any given point is what is called r_c . This is a small signal resistance; which is, r_c is nothing but ΔV_{CB} divided by ΔI_C ; change in the collector base voltage for a change in collector current, by definition, at a certain operating point. This is typically of the order of tens of megaohms.

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Let us try to learn more about this output resistance for this transistor, bipolar junction transistor. This effect that we are going to discuss is called Early's Effect. What is it? We know that... again, we will take the same p n p transistor that we have used earlier. This is the emitter current; we have the collector; we see most of the emitter carriers at the collector and very little of it is left as the base. Alpha, very typically, is made close to 1, when it is forward biased at the emitter base junction and reverse biased at the collector base junction.

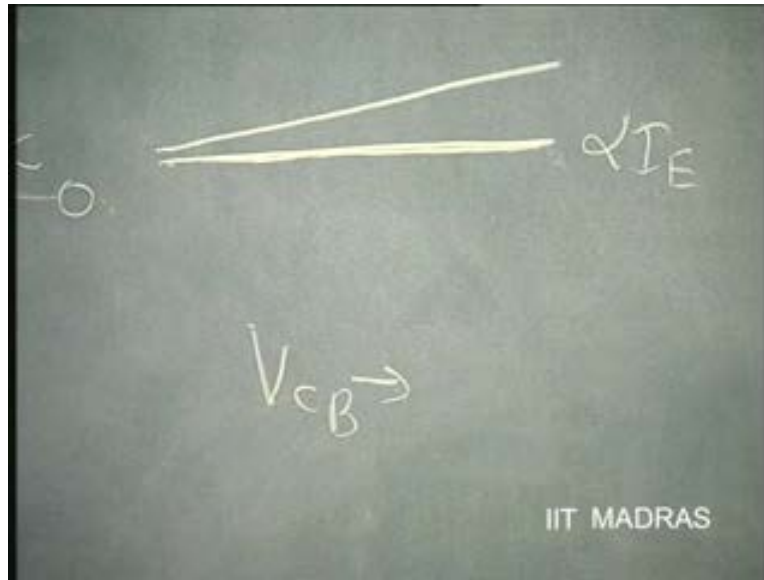
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Now, the depletion layer width here keeps increasing as this voltage V_{BC} keeps increasing. So, when this voltage V_{BC} increases, the depletion layer width increases. Now, what happens? Of course, the field here will assist; it will increase and it will assist these to fast come to this side. But, first of all, these things have to come to this side. That does not depend upon the field. But what happens here is that because **because** V_{BC} increases, the base width decreases; and those holes which are injected down to the base, a larger number of these will get collected here. That means Alpha is going to be becoming closer to 1.

So now, Alpha depends upon V_{CB} . That means Alpha will become closer to 1; or, I_C is going to increase as V_{CB} increases. This is what is called Early Effect. Is this clearly understood? Because the depletion layer width increases, the base transport factor is going to become closer to 1 as V_{CB} increases. That means I_C is going to increase because I_C is equal to Alpha times I_E . For the same I_E , let us say... earlier we said, for a given I_E , and this is V_{CB} variation, this is going to remain constant at Alpha times I_E . If Alpha is now going to increase as V_{CB} increases because of Early Effect, then what you will see is going to be the effect like this.

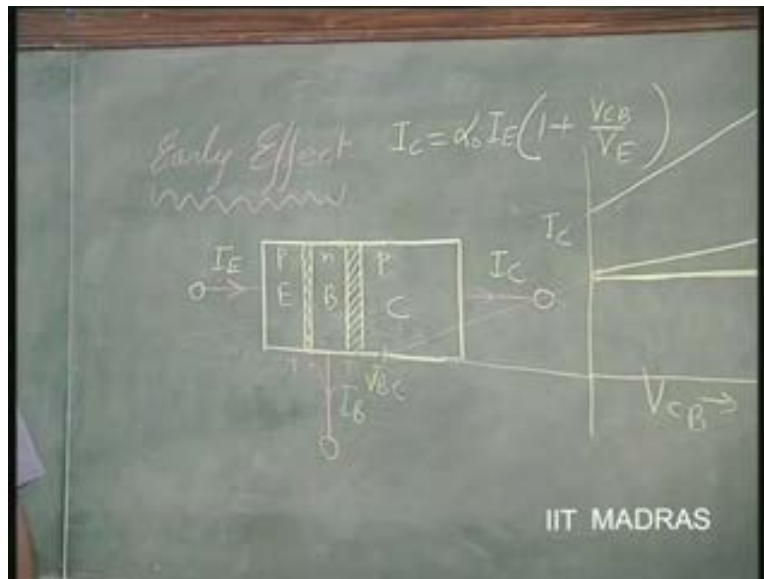
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That means, actually speaking, in our sort of characteristic curve, if this is I_C for different V_{CB} and for all values of I_E you are putting down here, these will go on increasing. Now, what happens because of Early Effect is, this effect is going to be felt more at higher currents; and therefore, this whole characteristic can be expanded like this and it will intersect at a particular point and this is called early voltage.

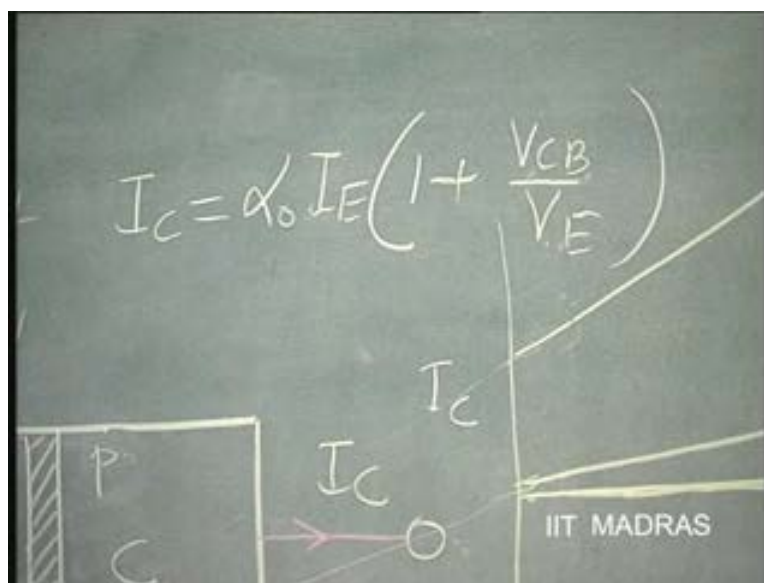
For the next current, it might be something like this and all these things will intersect at a particular point in this axis and that is called early's voltage; or mathematically, I can say, I_C is equal to αI_E , which is the independent factor compared to V_{CB} , $1 + V_{CB} / V_E$ where V_E is the early's voltage.

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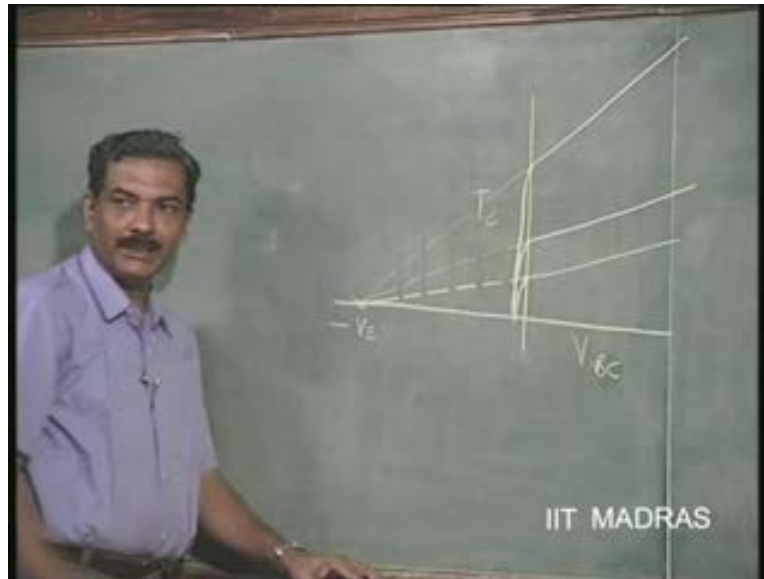
So, it is a factor dependent upon V_{CB} . For an ideal transistor where this effect is not there, V_E is infinity. So, I_C is equal to $\alpha_0 I_E$. Otherwise, it is $\alpha_0 I_E \left(1 + \frac{V_{CB}}{V_E}\right)$. α_0 is the α_0 which is independent of V_{CB} , into 1 plus V_{CB} divided by V_E . This voltage, V_E is called early voltage.

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So, once again, I can draw the characteristic here clearly to show you this is V_{CB} , I_C versus V_{CB} for different values of I_E . So, you will get something like this. You extend this. This is minus V_E . This **this** is actually V_{BC} . This is positive. V_{BC} is positive for p n p. So, for another transistor, another current, this is going to be the characteristics. For a lower current ... So, these are going to be extensions. Otherwise, actually, characteristic is going to... actual characteristic, because this is... this region, the transistor goes to saturation. So, this will be the actual characteristic. So, these extensions join at a particular point. This is an important voltage which is called early voltage.

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In our expression therefore, please remember. You have to give this value if you want to see this effect of output impedance. So, output impedance is nothing but what ΔV_{CB} divided by ΔI_C . So, that is equal to, let us say, ΔI_C by ΔV_{CB} is nothing but... from this expression, $\alpha \cdot I_E$ by V_E ; it is nothing but the coefficient of V_{CB} . So, V_E divided by α . So, given the early voltage as well as the operating current and α , we can find out the value of what? What is this? r_c .

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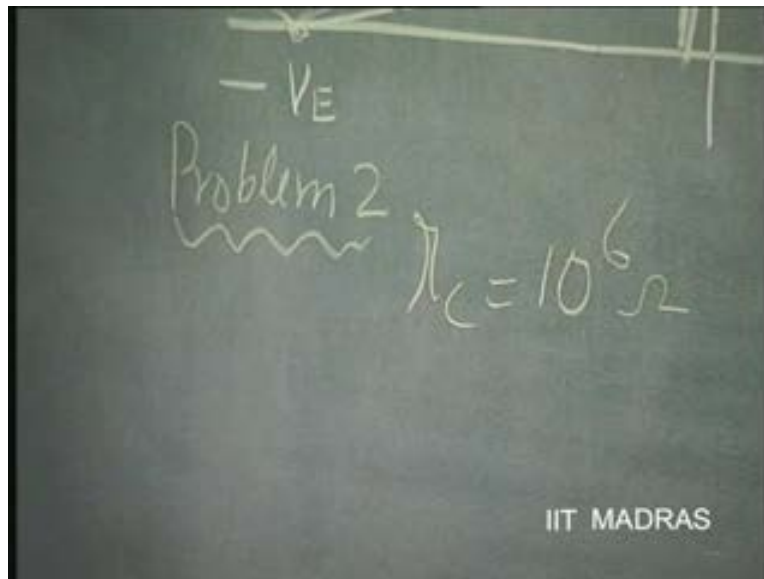
$$I_C = \alpha_0 I_E \left(1 + \frac{V_{CB}}{V_E} \right)$$
$$\frac{\partial V_{CB}}{\partial I_C} = \frac{V_E}{\alpha_0 I_E} = r_c$$

So, this is an important small signal parameter. If you are therefore analyzing your circuit using Spice programs, etcetera, you have to give the early voltage.

Now, I would like you to therefore compute the value of output impedance for the example that we have chosen, Example 10. Determine the output resistance if r_c is given as 1 megaohms. r_c is given as 1 megaohms. Determine the output resistance.

Now earlier, output resistance was 6 K for the example. Now, how much is it going to differ from 6 K? You will see that it is not going to differ much from 6 K in spite of the finite r_c of 1 mega ohm. So, but, you please use the equivalent circuit and find out for yourself. This will be worked out. This is a problem. This is problem, what is the number? – 2.

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Determine the output impedance for Example 10, if r_c is equal to 1 mega ohm.